

# Interface Text Search

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7631	Gaas.clm.	US-PGPUB; USPAT	OR	OFF	2006/02/08 11:04
L2	1950	AlGaAs.clm.	US-PGPUB; USPAT	OR	OFF	2006/02/08 11:04
L3	1730	Gaas near substrate.clm.	US-PGPUB; USPAT	OR	ON	2006/02/08 11:05
L5	128	(hfet heterojunction adj (fet field)). clm.	US-PGPUB; USPAT	OR	ON	2006/02/08 11:06
L6	11	5 and 3	US-PGPUB; USPAT	OR	ON	2006/02/08 11:06

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	(US-20040104404-\$ or US-20030132496-\$ or US-20020053682-\$ or US-20010019131-\$ or US-20010013604-\$ or US-20010005016-\$).did. or (EP-1424734-\$).did.	US-PGPUB; EPO	OR	OFF	2006/02/08 10:16
L2	5	L1 and Ingaas adj channel	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L3	1	jp-2001250939-\$	JPO; IBM_TDB	OR	OFF	2006/02/08 10:16
L4	414	(InP InGaP GaInP Ingaas GaAs) adj channel and (AlGaAs GaAlAs) and GaAs	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L5	2	(InP InGaP GaInP Ingaas GaAs) adj channel and ((AlGaAs GaAlAs) and GaAs) near3 etch adj stop	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L6	51	L4 and gate with p-type	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L7	20	(InP InGaP GaInP Ingaas GaAs) adj schottky adj layer	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L8	132	(InP InGaP GaInP Ingaas GaAs) with schottky adj layer	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L9	78	L8 and GaAs near3 substrate	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L10	45	L9 and @pd>"20011113"	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16

L11	11	L10 and p-type	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L12	34	L10 not L11	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L13	1	pj-hfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 10:16
L14	316	p-gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 10:16
L15	4	p-gate and heterojunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 10:16
L16	20648	jfet heterojunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 10:16
L17	271	jfet and heterojunction	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/08 10:16
L18	180	(InP InGaP GaInP Ingaas GaAs) and L17	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L19	99	L18 and (AlGaAs GaAlAs) and GaAs	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L20	11	"5161235" and (AlGaAs GaAlAs) and GaAs	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L21	0	(US-20050167698-\$).did.	US-PGPUB	OR	OFF	2006/02/08 10:16

L22	10	nishi.in. and (hemt hjfet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L23	1428	(gaas gallium adj arsenide) near2 substrate and (hemt hjfet heterojunction adj (field fet))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L24	14	"5548148"	US-PGPUB; USPAT	OR	OFF	2006/02/08 10:16
L25	1671	(257/192,194,195,280,284).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/08 10:16
L26	12	L24 and p-type	US-PGPUB; USPAT	OR	OFF	2006/02/08 10:16
L27	6	"4929985"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L28	75	barrier near4 (gainas ingaas) and hemt	US-PGPUB; USPAT	OR	OFF	2006/02/08 10:16
L29	11	"4849368"	US-PGPUB; USPAT	OR	OFF	2006/02/08 10:16
L30	128	(mesfet hemt) and recess with gate and n-type and p-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L31	33	p-jfet	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L32	123	jfet and algaas	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16
L33	121	L32 not L31	US-PGPUB; USPAT; EPO; DERWENT; IBM_TDB	OR	OFF	2006/02/08 10:16